

## Amended Abstract

~~The invention relates to a A method for self-supported transfer of a fine layer, wherein: in which at least one species of ions is implanted in a source-substrate at a given specified depth in relation to the surface of the source-substrate according to a certain dosage; A a stiffener is applied, which is in intimate contact with the source-substrate, is applied; said and the source-substrate undergoes a heat treatment at a given specified temperature during a specified given period of time in order to create an embrittled, buried area substantially at said given the specified depth without causing the a fine thin layer, defined between the surface and the embrittled buried layer in relation to the remainder of the source-substrate, to become thermally detached; A a controlled localized energy pulse is applied to the source-substrate in a temporarily localized manner in order to cause the self-supported detachment of a fine the thin layer which is defined between the surface and the embrittled buried layer in relation to the rest of the source-substrate.~~

## ABSTRACT

A method for self-supported transfer of a fine layer, in which at least one species of ions is implanted in a source-substrate at a specified depth in relation to the surface of the source-substrate. A stiffener is applied in intimate contact with the source-substrate and the source-substrate undergoes a heat treatment at a specified temperature during a specified period of time in order to create an embrittled buried area substantially at the specified depth without causing a thin layer, defined between the surface and the embrittled buried layer in relation to the remainder of the source-substrate, to become thermally detached. A controlled localized energy pulse is applied to the source-substrate in order to cause the self-supported detachment of the thin layer.